Atmel AT24C16C

I²C-Compatible, (2-Wire) Serial EEPROM 16-Kbit (2048 x 8)

DATASHEET

Standard Features

Atmel

- Low-voltage and standard-voltage operation
 - V_{CC} = 1.7V to 5.5V
- Internally organized as 2,048 x 8 (16K)
- I²C-compatible (2-wire) serial interface
- Schmitt Trigger, filtered inputs for noise suppression
- Bidirectional data transfer protocol
- 1MHz (2.5V, 2.7V, 5V), 400kHz (1.7V) compatibility
- Write Protect pin for hardware data protection
- 16-byte Page Write mode
- Partial page writes allowed
- Self-timed write cycle (5ms max)
- High-reliability
 - Endurance: 1,000,000 write cycles
 - Data retention: 100 years
- Green package options (Pb/Halide-free/RoHS compliant)
 - 8-lead PDIP, 8-lead SOIC, 8-lead TSSOP, 8-pad UDFN, 8-pad XDFN, 5-lead SOT23, and 8-ball VFBGA
- Die options: wafer form and tape and reel

Description

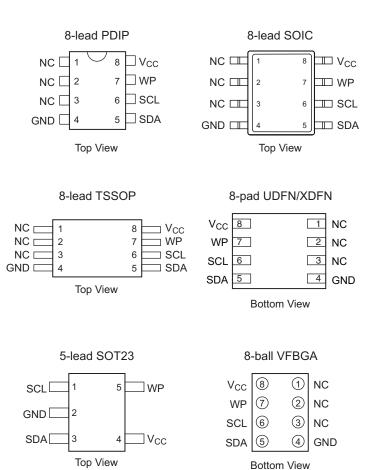
The Atmel[®] AT24C16C provides 16,384 bits of Serial Electrically Erasable and Programmable Read-Only Memory (EEPROM) organized as 2,048 words of eight bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. AT24C16C is available in space-saving 8-lead PDIP, 8-lead JEDEC SOIC, 8-lead TSSOP, 8-pad UDFN, 8-pad XDFN, 5-lead SOT23, and 8-ball VFBGA packages and is accessed via a 2-wire serial interface.

1. Pin Configurations and Pinouts

Pin Configuration

Table 1.

Pin Name	Function
NC	No Connect
SDA	Serial Data
SCL	Serial Clock Input
WP	Write Protect
GND	Ground
V _{CC}	Power Supply



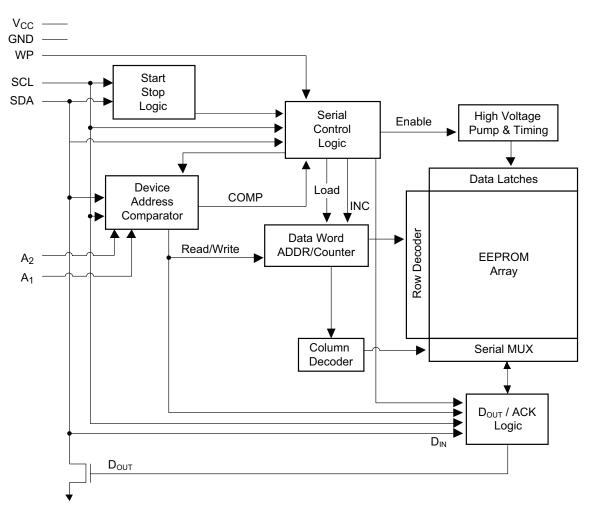
Note: Drawings are not to scale.

2. Absolute Maximum Ratings

Operating Temperature
Storage Temperature65°C to +150°C
Voltage on any pin with respect to ground
Maximum Operating Voltage 6.25V
DC Output Current

*Notice: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

3. Block Diagram



4. Pin Description

Serial Clock (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

Serial Data (SDA): The SDA pin is bidirectional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open-collector devices.

Device/Page Addresses: The AT24C16C does not use the device address pins, which limits the number of devices on a single bus to one (see Section 7. "Device Addressing" on page 9).

Write Protect (WP): AT24C16C has a Write Protect pin that provides hardware data protection. The Write Protect pin allows normal Read/Write operations when connected to Ground (GND). When the Write Protect pin is connected to V_{CC} , the Write Protection feature is enabled and operates as shown in Table 4-1.

	Part of the Array Protected
WP Pin Status	AT24C16C
At V _{CC}	Full Array
At GND	Normal Read/Write Operations

5. Memory Organization

AT24C16C, 16K Serial EEPROM: Internally organized with 128 pages of 16 bytes each, the 16K requires a 11-bit data word address for random word addressing.

Table 5-1. Pin Capacitance⁽¹⁾

Applicable over recommended operating range from $T_A = 25^{\circ}C$, f = 1.0MHz, $V_{CC} = 5.5V$.

Symbol	Test Condition	Max	Units	Conditions
C _{I/O}	Input/Output capacitance (SDA)	8	pF	V _{I/O} = 0V
C _{IN}	Input capacitance (A ₀ , A ₁ , A ₂ , SCL)	6	pF	$V_{IN} = 0V$

Note: 1. This parameter is characterized and is not 100% tested.

Table 5-2. DC Characteristics

Applicable over recommended operating range from: $T_{AI} = -40^{\circ}$ C to $+85^{\circ}$ C, $V_{CC} = 1.7$ V to 5.5V (unless otherwise noted).

Symbol	Parameter	Test Condition	Min	Тур	Max	Units
V _{CC1}	Supply Voltage		1.7		5.5	V
I _{CC}	Supply Current V_{CC} = 5.0V	Read at 100kHz		0.4	1.0	mA
I _{CC}	Supply Current V_{CC} = 5.0V	Write at 100kHz		2.0	3.0	mA
I _{SB1}	Standby Current V _{CC} = 1.7V	$V_{IN} = V_{CC} \text{ or } V_{SS}$			1.0	μA
I _{SB2}	Standby Current V_{CC} = 5.5V	$V_{IN} = V_{CC} \text{ or } V_{SS}$			6.0	μA
I _{LI}	Input Leakage Current	$V_{IN} = V_{CC} \text{ or } V_{SS}$		0.10	3.0	μA
I _{LO}	Output Leakage Current	$V_{OUT} = V_{CC} \text{ or } V_{SS}$		0.05	3.0	μA
V _{IL}	Input Low Level ⁽¹⁾		-0.6		V _{CC} x 0.3	V
V _{IH}	Input High Level ⁽¹⁾		V _{CC} x 0.7		V _{CC} + 0.5	V
V _{OL2}	Output Low Level V_{CC} = 3.0V	I _{OL} = 2.1mA			0.4	V
V _{OL1}	Output Low Level V _{CC} = 1.7V	I _{OL} = 0.15mA			0.2	V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

Table 5-3. AC Characteristics

Applicable over recommended operating range from T_{AI} = -40°C to 85°C, V_{CC} = +1.7V to 5.5V, CL = 1TTL Gate and 100pF (unless otherwise noted).

		1.7V		2.5V, 2.7	7V, 5.0V	
Symbol	Parameter	Min	Max	Min	Мах	Units
f _{SCL}	Clock Frequency, SCL		400		1000	kHz
t _{LOW}	Clock Pulse Width Low			0.4		μs
t _{HIGH}	Clock Pulse Width High			0.4		μs
t _i	Noise Suppression Time		100		50	ns
t _{AA}	Clock Low to Data Out Valid	0.1	0.9	0.05	0.55	μs
t _{BUF}	Time the bus must be free before a new transmission can start.	1.2		0.5		μs
t _{HD.STA}	Start Condition Hold Time	0.6		0.25		μs
t _{SU.STA}	Start Condiition Setup Time	0.6		0.25		μs
t _{HD.DAT}	Data In Hold Time	0		0		μs
t _{SU.DAT}	Data In Setup Time	100		100		ns
t _R	Inputs Rise Time ⁽¹⁾		0.3		0.3	μs
t _F	Inputs Fall Time ⁽¹⁾		300		100	ns
t _{SU.STO}	Stop Condition Setup Time	0.6		.25		μs
t _{DH}	Data Out Hold Time	50		50		ns
t _{wR}	Write Cycle Time		5		5	ms
Endurance ⁽¹⁾	3.3V, 25°C, Page Mode		1,000	0,000		Write Cycles

Note: 1. This parameter is ensured by characterization only.

6. Device Operation

Clock and Data Transitions: The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (see Figure 6-4 on page 8). Data changes during SCL high periods will indicate a Start or Stop Condition as defined below.

Start Condition: A high-to-low transition of SDA with SCL high is a Start Condition which must precede any other command (see Figure 6-5 on page 8).

Stop Condition: A low-to-high transition of SDA with SCL high is a Stop Condition. After a read sequence, the Stop Condition command will place the EEPROM in a standby power mode (see Figure 6-5 on page 8).

Acknowledge: All addresses and data words are serially transmitted to and from the EEPROM in eight bit words. The EEPROM sends a zero to acknowledge that it has received each word. This happens during the ninth clock cycle.

Standby Mode: The AT24C16C features a low-power standby mode which is enabled:

- Upon power-up.
- After the receipt of the Stop Condition and the completion of any internal operations.

2-wire Software Reset: After an interruption in protocol, power loss or system reset, any 2-wire part can be reset by following these steps:

- 1. Create a Start Condition,
- 2. Clock nine cycles,
- 3. Create another Start Condition followed by Stop Condition as shown below.

The device is ready for next communication after above steps have been completed.

Figure 6-1. Software Reset

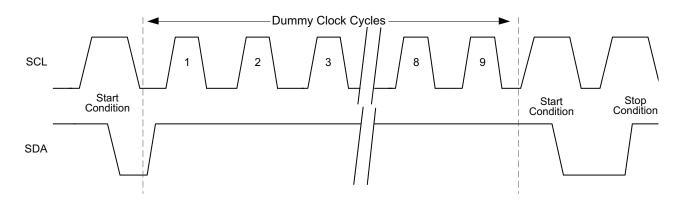
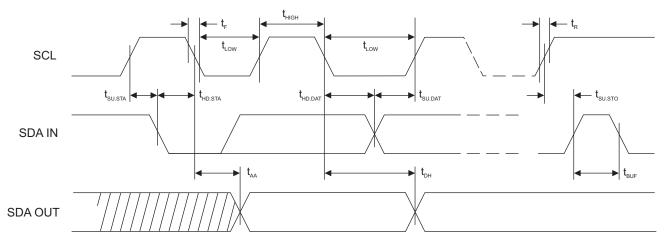


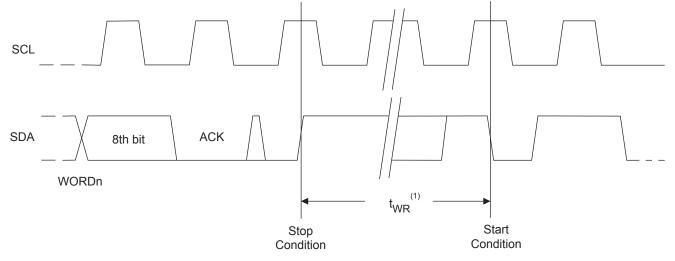
Figure 6-2. Bus Timing



SCL: Serial Clock, SDA: Serial Data I/O

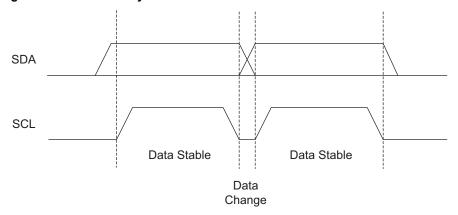
Figure 6-3. Write Cycle Timing

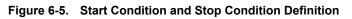
SCL: Serial Clock, SDA: Serial Data I/O

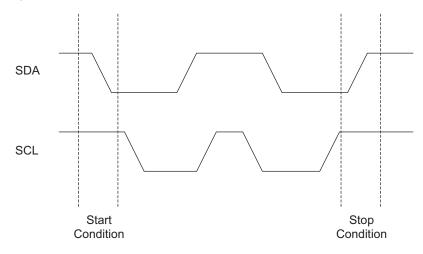


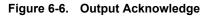
Notes: 1. The write cycle time t_{WR} is the time from a valid Stop Condition of a Write sequence to the end of the internal clear/write cycle.

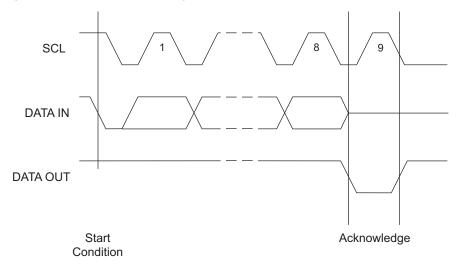
Figure 6-4. Data Validity













7. Device Addressing

Standard EEPROM Access: The 16K EEPROM device requires an 8-bit device address word following a Start Condition to enable the chip for a Read or Write operation. The device address word consists of a mandatory "1010" (Ah) sequence for the first four Most Significant Bits (MSB) as shown in Figure 10. on page 12. This is common to all the EEPROM devices.

The next three bits used for memory page addressing are the most significant bits of the data word address which follows.

The eighth bit of the device address is the Read/Write operation select bit. A Read operation is initiated if this bit is high and a Write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a zero. If a compare is not made, the chip will return to a standby state.

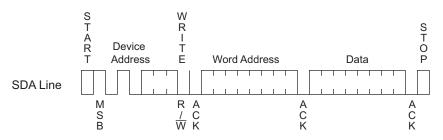
Figure 7-1. Device Address

Density	Access Area	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
16K	EEPROM	1	0	1	0	P2	P1	P0	R/W
	· ·	MSB			,				LSB

8. Write Operations

Byte Write: A Write operation requires an 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a zero and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a zero and the addressing device, such as a microcontroller, must terminate the Write sequence with a Stop Condition. At this time the EEPROM enters an internally timed write cycle, t_{WR}, to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the Write is complete (see Figure 8-1).

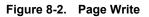
Figure 8-1. Byte Write

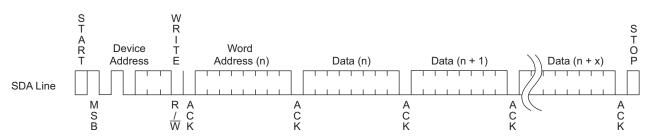


Page Write: The 16K EEPROM devices are capable of a 16-byte Page Write.

A Page Write is initiated in the same way as a Byte Write, but the microcontroller does not send a Stop Condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to fifteen more data words. The EEPROM will respond with a zero after each data word received. The microcontroller must terminate the Page Write sequence with a Stop Condition (see Figure 8-2).

The data word address lower four bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than eight data words are transmitted to the EEPROM, the data word address will roll-over and previous data will be overwritten.





Acknowledge Polling: Once the internally timed write cycle has started and the EEPROM inputs are disabled, Acknowledge Polling can be initiated. This involves sending a Start Condition followed by the device address word. The Read/Write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a zero allowing the Read or Write sequence to continue.

9. Read Operations

Read operations are initiated in the same way as Write operations with the exception that the Read/Write select bit in the device address word is set to one. There are three read operations:

- Current Address Read
- Random Address Read
- Sequential Read.

Current Address Read: The internal data word address counter maintains the last address accessed during the last Read or Write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address roll-over during Read is from the last byte of the last memory page to the first byte of the first page. The address roll-over during Write is from the last byte of the current page to the first byte of the same page.

Once the device address with the Read/Write select bit set to one is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input zero but does generate a following Stop Condition (see Figure 9-1).

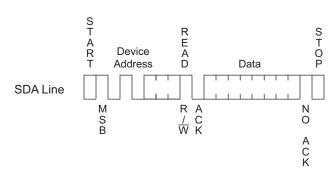
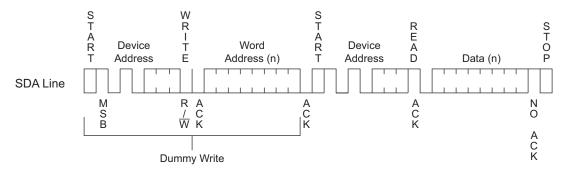


Figure 9-1. Current Address Read

Random Read: A Random Read requires a Dummy Byte Write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another Start Condition. The microcontroller now initiates a Current Address Read by sending a device address with the Read/Write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a zero but does generate a following Stop Condition (see Figure 9-2).





Sequential Read: Sequential Reads are initiated by either a Current Address Read or a Random Address Read. After the microcontroller receives a data word, it responds with an Acknowledge. As long as the EEPROM receives an Acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will roll-over and the Sequential Read will continue. The Sequential Read operation is terminated when the microcontroller does not respond with a zero but does generate a following Stop Condition (see Figure 9-3).

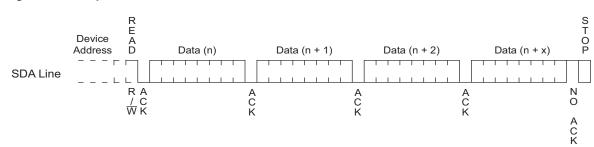
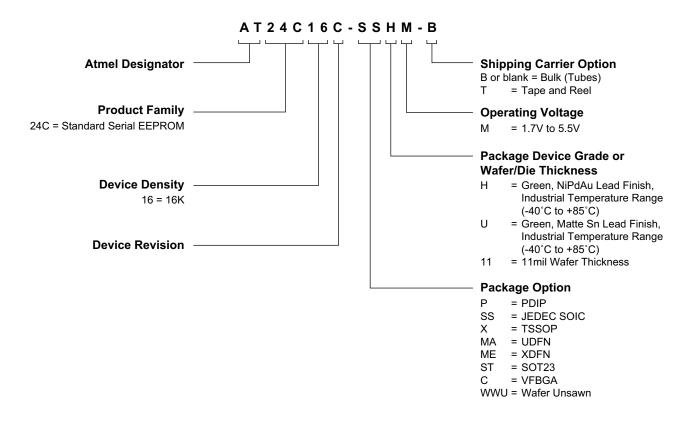


Figure 9-3. Sequential Read

10. Ordering Code Detail



11. Product Markings

8-lead PDIP	8-lead SOIC		8-lead TSSOP	8	8-pad UDF	N
ATMLUYWW ###% AAAAAAA U U U U	ATMLI ###% AAAA		ATHYWW ###% @ AAAAAAA		H	### H%@ YXX
8-pad XDFN	5-lead SOT-2	3	8-ball VFBGA			
1.8 x 2.2 mm Body ### YXX ●	Н. Н. (###%U) Н. Н. Н. УМХХ Н. Н. Н. Н.	Top Mark Bottom Mark	1.5 x 2.0 mm Body			
Note 1: designates pin 1 Note 2: Package drawings are not to so Catalog Number Trunc		-				
Note 2: Package drawings are not to so Catalog Number Trunc AT24C16C Date Codes	ation	1	n Code ###: 16C	Voltag		
Note 2: Package drawings are not to so		1	rk Week of Assembly 2 4	%		m Voltage
Note 2: Package drawings are not to se Catalog Number Trunc AT24C16C Date Codes Y = Year 3: 2013 7: 2017 4: 2014 8: 2018 5: 2015 9: 2019 5: 2016 0: 2020	M = Month A: January B: February L: December	WW = Wc 02: Week 04: Week 	rk Week of Assembly 2 4	M	5 = Minimu : 1.7V m	
Note 2: Package drawings are not to so Catalog Number Trunc AT24C16C Date Codes Y = Year 3: 2013 7: 2017 4: 2014 8: 2018 5: 2015 9: 2019 5: 2016 0: 2020 Country of Assembly	M = Month A: January B: February L: December Lot N	WW = Wc 02: Week 04: Week 52: Week	rk Week of Assembly 2 4	% M Grade	5 = Minimu 1.7V m /Lead Fini	in ish Material al/NiPdAu
Note 2: Package drawings are not to se Catalog Number Trunc AT24C16C Date Codes Y = Year 3: 2013 7: 2017 4: 2014 8: 2018 5: 2015 9: 2019 5: 2016 0: 2020 Country of Assembly @ = Country of Assembly	M = Month A: January B: February L: December Lot N	WW = Wc 02: Week 04: Week 52: Week	rk Week of Assembly 2 4 52	Grade. H U	5 = Minimu 1.7V m /Lead Fini 1. Industri 1. Industri	in ish Material al/NiPdAu al/Matte Tin/Sn,
Note 2: Package drawings are not to se Catalog Number Trunc AT24C16C Date Codes Y = Year 3: 2013 7: 2017 4: 2014 8: 2018 5: 2015 9: 2019 5: 2016 0: 2020 Country of Assembly @ = Country of Assemble	M = Month A: January B: February L: December Lot Numbers Correspondent	WW = Wc 02: Week 04: Week 52: Week Iumber A = Atmel Wa	rk Week of Assembly 2 4 52	Grade Grade H U Atmel	5 = Minimu 1.7V m /Lead Fini	in ish Material al/NiPdAu al/Matte Tin/Sn
Note 2: Package drawings are not to sc Catalog Number Trunc T24C16C Date Codes (= Year : 2013 7: 2017 : 2014 8: 2018 : 2015 9: 2019 : 2016 0: 2020 Country of Assembly D = Country of Assemble Trace Code (X = Trace Code (Atmel	M = Month A: January B: February L: December Lot Numbers Correspondent	WW = Wc 02: Week 04: Week 52: Week Iumber A = Atmel Wa	rk Week of Assembly 2 4 52	Grade Grade H U Atmel	5 = Minimu 1.7V m /Lead Fini Industri Industri Truncatio Truncatio Atmel Atmel	in ish Material al/NiPdAu al/Matte Tin/Sn
Note 2: Package drawings are not to se Catalog Number Trunc AT24C16C Date Codes (= Year 3: 2013 7: 2017 4: 2014 8: 2018 5: 2015 9: 2019 5: 2016 0: 2020 Country of Assembly @ = Country of Assembly Trace Code (X = Trace Code (Atmediated Atmediated	M = Month A: January B: February L: December Lot Numbers Correspondent	WW = Wc 02: Week 04: Week 52: Week Iumber A = Atmel Wa	rk Week of Assembly 2 4 52	Grade Grade H U Atmel	5 = Minimu 1.7V m /Lead Fini Industri Industri Truncatio Truncatio Atmel Atmel	in ish Material al/NiPdAu al/Matte Tin/Sn,

12. Ordering Codes

12.1 AT24C16C Ordering Information

Atmel Ordering Code	Lead Finish	Package	Voltage	Operation Range
AT24C16C-PUM	Bulk Form Only (Lead-free/Halogen-free)	8P3	-	
AT24C16C-SSHM-B ⁽¹⁾		8S1		
AT24C16C-SSHM-T ⁽²⁾	NiPdAu (Lead-free/Halogen-free)	001		
AT24C16C-XHM-B ⁽¹⁾		8X	1.7V to 5.5V	
AT24C16C-XHM-T ⁽²⁾		07		Industrial Temperature
AT24C16C-MAHM-T ⁽²⁾		8MA2		(–40°C to 85°C)
AT24C16C-MEHM-T ⁽²⁾	_	8ME1		
AT24C16C-STUM-T ⁽²⁾	Matte Sn (Lead-free/Halogen-free)	5TS1		
AT24C16C-CUM-T ⁽²⁾	SnAgCu (Lead-free/Halogen-free)	8U3-1		
AT24C16C-WWU11M ⁽³⁾		Wafer Sale		

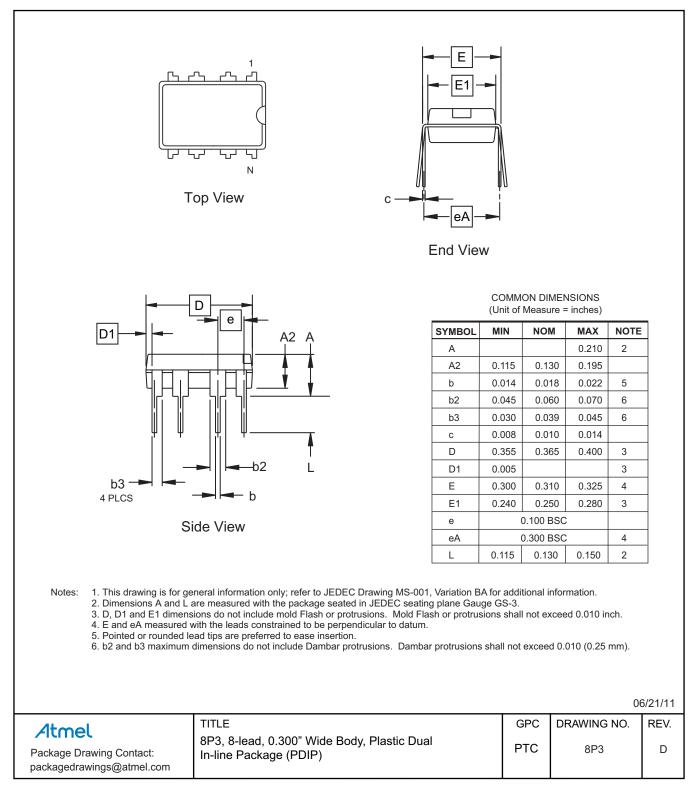
Notes: 1. B = Bulk

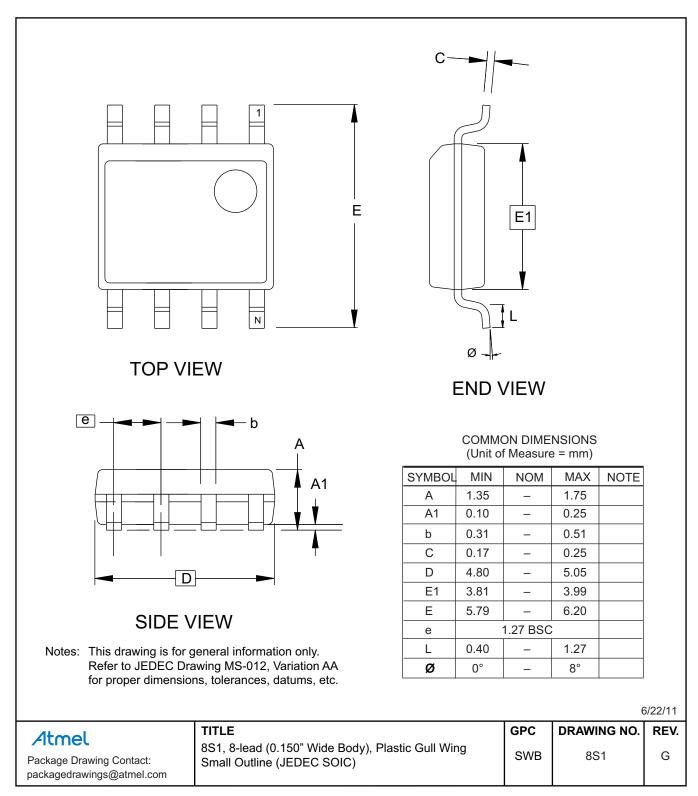
- 2. T = Tape and Reel
 - SOIC = 4K per reel
 - TSSOP, UDFN, XDFN, SOT23, and VFBGA = 5K per reel
- 3. For Wafer sales, please contact Atmel Sales.

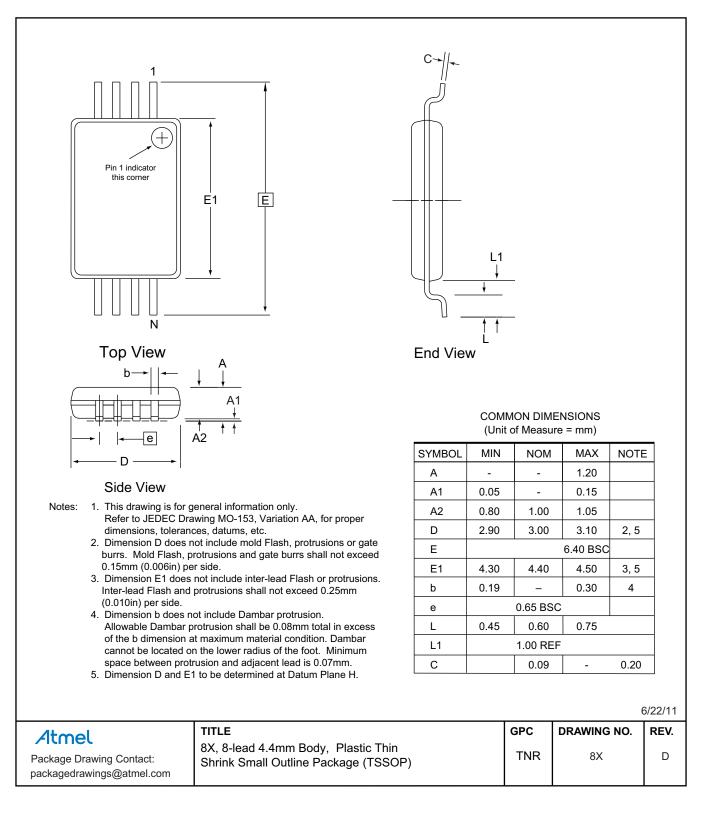
	Package Type
8P3	8-lead, 0.300" wide, Plastic Dual Inline (PDIP)
8S1	8-lead, 0.150" wide, Plastic Gull Wing Small Outline (JEDEC SOIC)
8X	8-lead, 4.40mm body, Plastic Thin Shrink Small Outline (TSSOP)
8MA2	8-pad, 2.00mm x 3.00mm body, 0.50mm pitch, Plastic Ultra Thin Dual Flat No Lead (UDFN)
8ME1	8-lead, 1.80mm x 2.20mm body, 0.40mm pitch, Extra Thin Dual Flat No Lead (XDFN)
5TS1	5-lead, 2.90mm x 1.60mm body, Plastic Thin Shrink Small Outline (SOT23)
8U3-1	8-ball, 1.50mm x 2.00mm body, 0.50mm pitch, Die Ball Grid Array (VFBGA)

13. Packaging Information

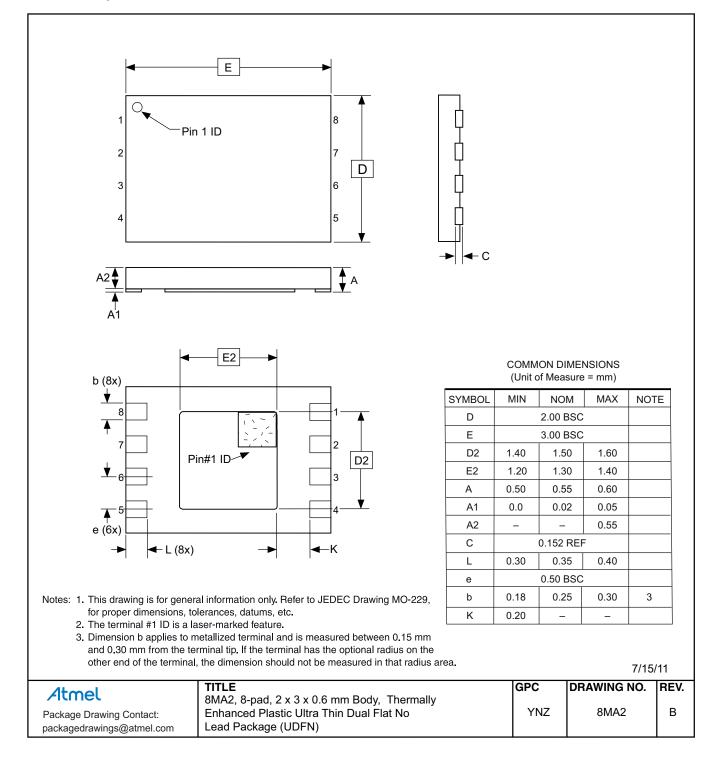
8P3 — 8-lead PDIP

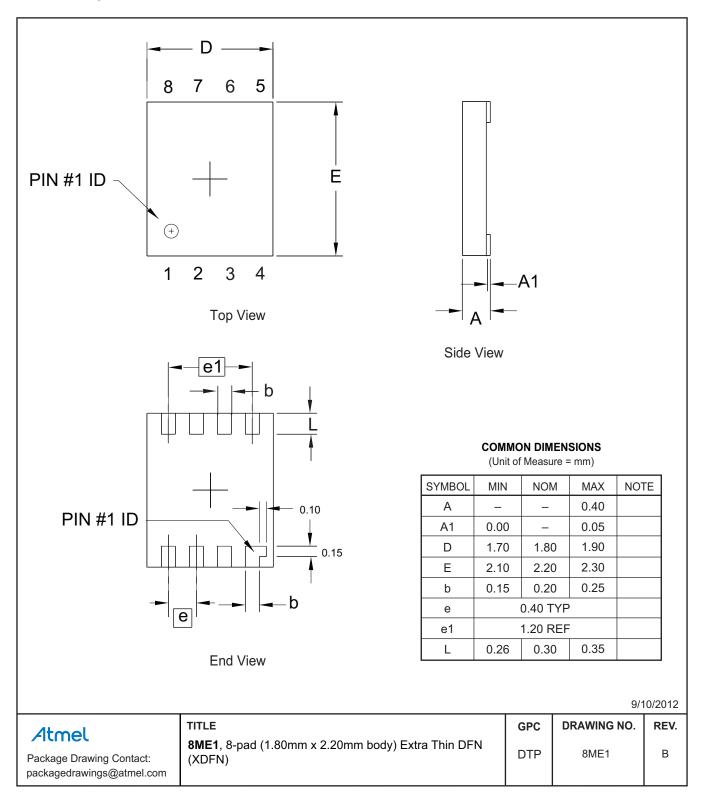




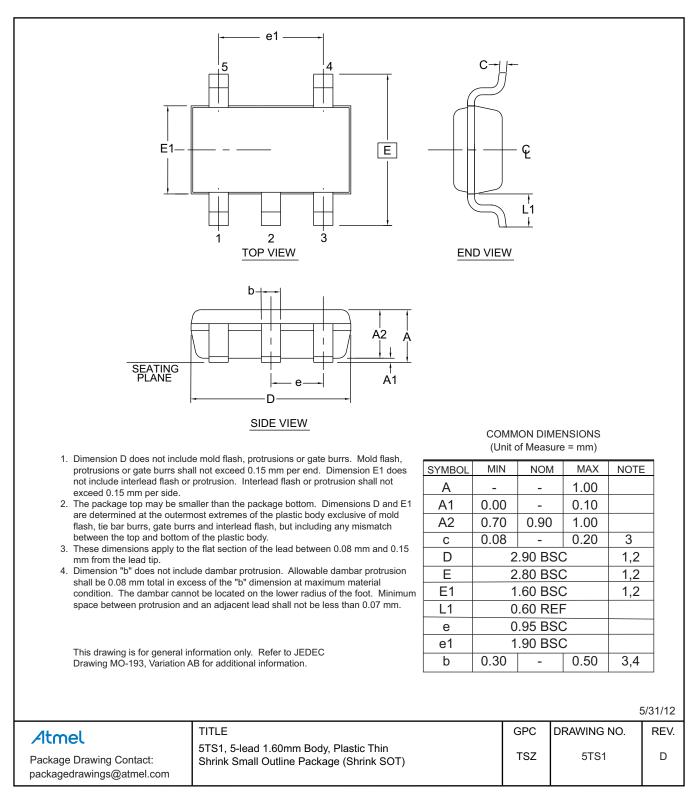


13.3 8MA2 — 8-pad UDFN

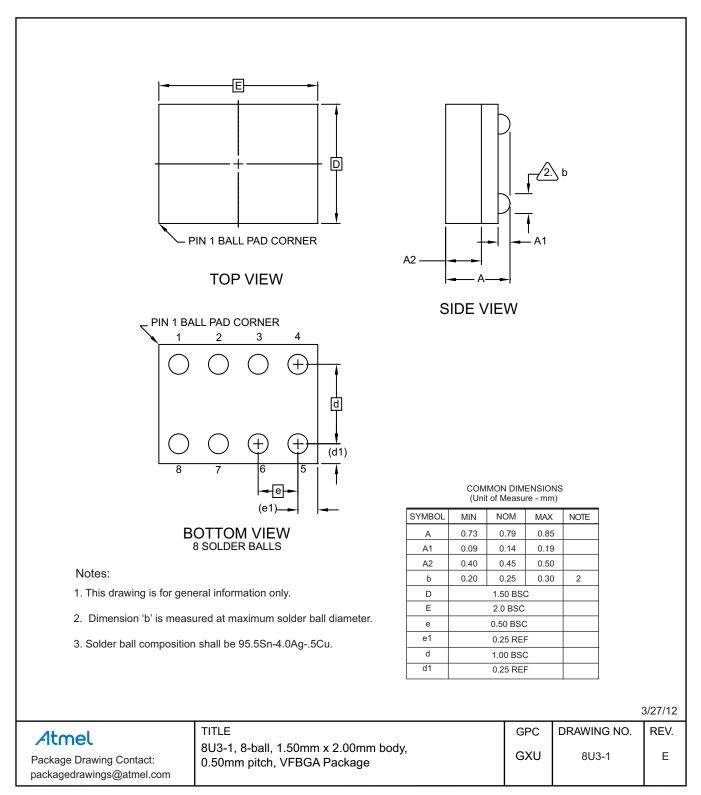




13.5 5TS1 — 5-lead SOT23



13.6 8U3-1 - 8-ball VFBGA



14. Revision History

Doc. Rev.	Date	Comments
8719B	07/2013	Minor grammetical corrections. Update Atmel logos and template.
8719A	09/2010	Initial document release.

Atmel Enabling Unlimited Possibilities®



Atmel Corporation 1600 Technology Drive, San Jose, CA 95110 USA T: (+1)(408) 441.0311 F: (+1)(408) 436.4200

| www.atmel.com

© 2013 Atmel Corporation. All rights reserved. / Rev.: Atmel-8719B-SEEPROM-AT24C16C-Datasheet_042013.

Atmel[®], Atmel logo and combinations thereof, Enabling Unlimited Possibilities[®], and others are registered trademarks or trademarks of Atmel Corporation or its subsidiaries. Other terms and product names may be trademarks of others.

DISCLAIMER: The information in this document is provided in connection with Atmel products. No license, express or implied, by estoppel or otherwise, to any intellectual property right is granted by this document or in connection with the sale of Atmel products. EXCEPT AS SET FORTH IN THE ATMEL TERMS AND CONDITIONS OF SALES LOCATED ON THE ATMEL WEBSITE, ATMEL ASSUMES NO LIABILITY WHATSOEVER AND DISCLAIMS ANY EXPRESS, IMPLIED OR STATUTORY WARRANTY RELATING TO ITS PRODUCTS INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTY OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT. IN NO EVENT SHALL ATMEL BE LIABLE FOR ANY DIRECT, INDIRECT, CONSEQUENTIAL, PUNITIVE, SPECIAL OR INCIDENTAL DAMAGES (INCLUDING, WITHOUT LIMITATION, OR LOSS OF INFORMATION) ARISING OUT OF THE USE OR INABILITY TO USE THIS DOCUMENT, EVEN IF ATMEL HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGES. Atmel makes no representations or warranties with respect to the accuracy or completeness of the contents of this document and reserves the right to make changes to specifications and products descriptions at any time without notice. Atmel does not make any commitment to update the information contained herein. Unless specifically provided otherwise, Atmel products are not suitable for, and shall not be used in, automotive applications. Atmel products are not intended, authorized, or warranted for use as components in applications intended to support or sustain life.

SAFETY-CRITICAL, MILITARY, AND AUTOMOTIVE APPLICATIONS DISCLAIMER: Atmel products are not designed for and will not be used in connection with any applications where the failure of such products would reasonably be expected to result in significant personal injury or death ("Safety-Critical Applications") without an Atmel officer's specific written consent. Safety-Critical Applications include, without limitation, life support devices and systems, equipment or systems for the operation of nuclear facilities and weapons systems. Atmel products are not designed nor intended for use in military or aerospace applications or environments unless specifically designated by Atmel as military-grade. Atmel products are not designed nor intended for use in automotive applications unless specifically designated by Atmel as automotive-grade.